# 74HC139; 74HCT139

### Dual 2-to-4 line decoder/demultiplexer

Rev. 4 — 11 December 2015

**Product data sheet** 

## 1. General description

The 74HC139; 74HCT139 decodes two binary weighted address inputs (nA0, nA1) to four mutually exclusive outputs ( $n\overline{Y}0$  to  $n\overline{Y}3$ ). Each decoder features an enable input ( $n\overline{E}$ ). When  $n\overline{E}$  is HIGH all outputs are forced HIGH. The enable input can be used as the data input for a 1-to-4 demultiplexer application. Inputs include clamp diodes. This enables the use of current limiting resistors to interface inputs to voltages in excess of  $V_{CC}$ .

#### 2. Features and benefits

- Input levels:
  - ♦ For 74HC139: CMOS level
  - ♦ For 74HCT139: TTL level
- Demultiplexing capability
- 2 independent 2-to-4 decoders
- Multifunction capability
- Suitable for memory decoding, data routing or code conversion
- Complies with JEDEC standard no. 7A
- Active LOW mutually exclusive outputs
- ESD protection:
  - ♦ HBM JESD22-A114F exceeds 2000 V
  - MM JESD22-A115-A exceeds 200 V
- Multiple package options
- Specified from -40 °C to +85 °C and from -40 °C to +125 °C

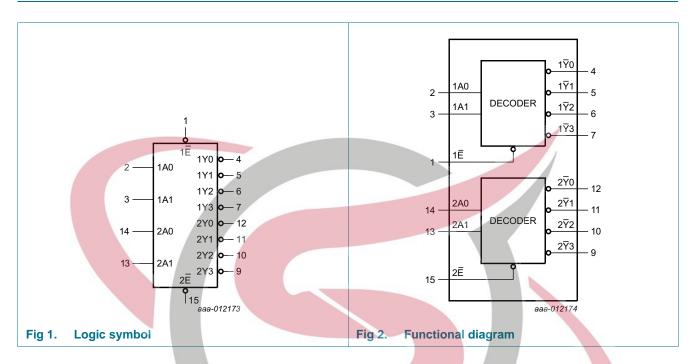
# 3. Ordering information

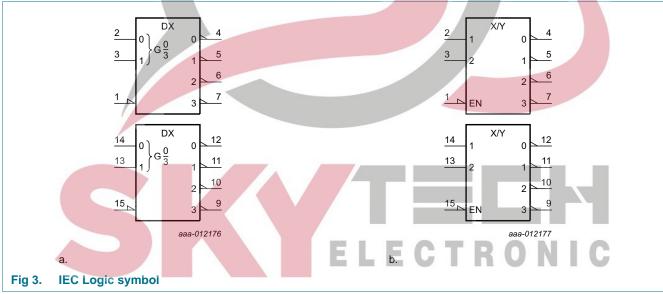
Table 1. Ordering information

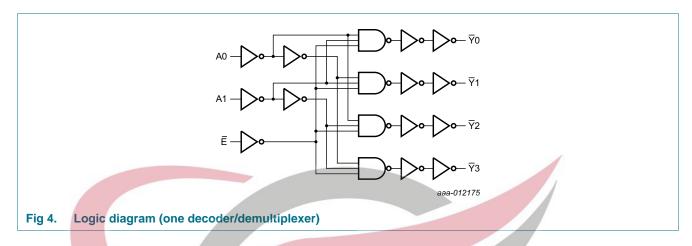
Type number	Package	Package Package									
	Temperature range	Name	Description	Version							
74HC139D	-40 °C to +125 °C	SO16	plastic small outline package; 16 leads;	SOT109-1							
74 HCT139D			body width 3.9 mm								
74HC139DB	−40 °C to +125 °C	SSOP16	plastic shrink small outline package; 16 leads;	SOT338-1							
74HCT139DB			body width 5.3 mm								
74HC139PW	-40 °C to +125 °C	TSSOP16	plastic thin shrink small outline package;	SOT403-1							
74HCT139PW			16 leads; body width 4.4 mm								



# 4. Functional diagram

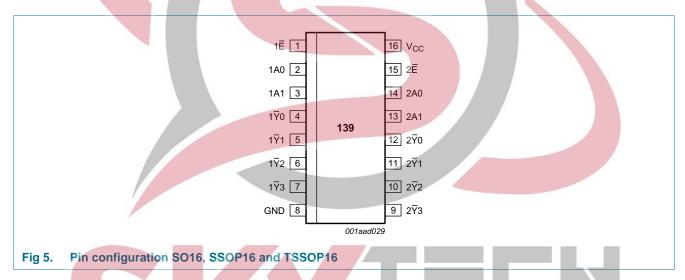






# 5. Pinning information

## 5.1 Pinning



### 5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
1E, 2E	1, 15	enable input (active LOW)
1A0, 1A1	2, 3	address input
1 <del>Y</del> 0, 1 <del>Y</del> 1, <del>1Y</del> 2, <del>1Y</del> 3	4, 5, 6, 7	output (active LOW)
GND	8	ground (0 V)
2 <del>Y</del> 0, <del>2</del> Y1, <del>2</del> Y2, <del>2</del> Y3	12, 11, 10, 9	output (active LOW)
2A0, 2A1	14, 13	address input
V <sub>CC</sub>	16	positive supply voltage

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# 6. Functional description

Table 3. Function table[1]

Control	Input Output					
nE	nA1	nA0	nY3	nY2	nY1	nY0
Н	X	X	Н	Н	Н	Н
L	L	L	Н	Н	Н	L
L	L	Н	Н	Н	L	Н
L	Н		Н	L	Н ,	Н
L	Н	Н	L	Н	H	Н

<sup>[1]</sup> H = HIGH voltage level;

### 7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC}$	supply voltage		-0.5	+7	V
I <sub>IK</sub>	input clamping current	$V_{I} < -0.5 \text{ V or } V_{I} > V_{CC} + 0.5 \text{ V}$	-	±20	mA
I <sub>OK</sub>	output clamping current	$V_{O} < -0.5 \text{ V or } V_{O} > V_{CC} + 0.5 \text{ V}$	-	±20	mA
Io	output current	$V_{\rm O} = -0.5 \text{ V to } (V_{\rm CC} + 0.5 \text{ V})$	-	±25	mA
I <sub>CC</sub>	quiescent supply current			50	mA
I <sub>GND</sub>	ground current		-50	<u>-</u>	mA
T <sub>stg</sub>	storage temperature		-65	+150	°C
P <sub>tot</sub>	total power dissipation	SO16 package [1]	-	500	mW
		SSOP16 package	-	500	mW
		TSSOP16 package	-	500	mW

<sup>[1]</sup> For SO16 package: Ptot derates linearly with 8 mW/K above 70 °C.

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L = LOW voltage level;

X = don't care.

<sup>[2]</sup> For SSOP16 and TSSOP16 packages: Ptot derates linearly with 5.5 mW/K above 60 °C.

# 8. Recommended operating conditions

Table 5. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V)

Symbol	Parameter	Conditions		74HC139	)	74HCT139			Unit
			Min	Тур	Max	Min	Тур	Max	
V <sub>CC</sub>	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
VI	input voltage		0	-	V <sub>CC</sub>	0	-	V <sub>CC</sub>	V
Vo	output voltage		0	-	V <sub>CC</sub>	0	-	V <sub>CC</sub>	V
T <sub>amb</sub>	ambient temperature		-40	+25	+125	-40	+25	+125	°C
Δt/ΔV	input transition rise and fall rate	$V_{CC} = 2.0 \text{ V}$	-	-	625	-//	-	-	ns/V
1		$V_{CC} = 4.5 \text{ V}$	-	1.67	139	-/	1.67	139	ns/V
		$V_{CC} = 6.0 \text{ V}$	-	-	83	-/	-	-	ns/V

# 9. Static characteristics

#### Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	T <sub>ar</sub>	<sub>nb</sub> = 25	°C	T <sub>amb</sub> = -		T <sub>amb</sub> = - +12		Unit
			Min	Тур	Max	Min	Max	Min	Max	
74HC139	9									
V <sub>IH</sub>	HIGH-level	V <sub>CC</sub> = 2.0 V	1.5	1.2	-	1.5	-	1.5	-	V
	input voltage	$V_{CC} = 4.5 \text{ V}$	3.15	2.4	-	3.15	-	3.15	-/	V
		$V_{CC} = 6.0 \text{ V}$	4.2	3.2	-4	4.2	-	4.2	<b>/-</b>	V
V <sub>IL</sub>	LOW-level	V <sub>CC</sub> = 2.0 V	-	0.8	0.5		0.5	-	0.5	V
	input voltage	V <sub>CC</sub> = 4.5 V	_	2.1	1.35	-	1.35	-	1.35	V
		V <sub>CC</sub> = 6.0 V	-	2.8	1.8	-	1.8	-	1.8	V
V <sub>OH</sub>	HIGH-level	$V_I = V_{IH}$ or $V_{IL}$								
	output voltage	$I_{O} = -20 \mu A; V_{CC} = 2.0 V$	1.9	2.0		1.9	-	1.9		V
		$I_{O} = -20 \mu A; V_{CC} = 4.5 V$	4.4	4.5	I - !	4.4	-	4.4		V
		$I_{O} = -20 \mu A$ ; $V_{CC} = 6.0 \text{ V}$	5.9	6.0		5.9	_	5.9		V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	3.98	4.32		3.84	B C	3.7		V
		$I_{O} = -5.2 \text{ mA}; V_{CC} = 6.0 \text{ V}$	5.48	5.81		5.34	H C	5.2		V
$V_{OL}$	LOW-level	$V_I = V_{IH}$ or $V_{IL}$								
	output voltage	$I_O = 20 \mu A; V_{CC} = 2.0 \text{ V}$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 20 \mu A; V_{CC} = 4.5 V$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 20 \mu A; V_{CC} = 6.0 \text{ V}$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 4.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	0.15	0.26	-	0.33	-	0.4	V
		$I_{O} = 5.2 \text{ mA}; V_{CC} = 6.0 \text{ V}$	-	0.16	0.26	-	0.33	-	0.4	V
l <sub>l</sub>	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 6.0 \text{ V}$	-	-	±0.1	-	±1.0	-	±1.0	μΑ
l <sub>OZ</sub>	OFF-state output current	$V_I = V_{IH}$ or $V_{IL}$ ; $V_O = V_{CC}$ or GND; $V_{CC} = 6.0 \text{ V}$	-	-	±0.5	-	±5.0	-	±10.0	μА

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 Table 6.
 Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Tar	<sub>mb</sub> = 25	°C	T <sub>amb</sub> = -4		T <sub>amb</sub> = -	40 °C to 5 °C	Unit
			Min	Тур	Max	Min	Max	Min	Max	
I <sub>CC</sub>	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 6.0 \text{ V}$	-	-	8.0	-	80	-	160	μΑ
Cı	input capacitance		-	3.5	-	-	-	-	-	pF
74HCT13	39							1.		
V <sub>IH</sub>	HIGH-level input voltage	V <sub>CC</sub> = 4.5 V to 5.5 V	2.0	1.6		2.0		2.0	-	V
V <sub>IL</sub>	LOW-level input voltage	V <sub>CC</sub> = 4.5 V to 5.5 V	-	1.2	0.8	-	0.8	-	0.8	V
V <sub>OH</sub>	HIGH-level	$V_I = V_{IH}$ or $V_{IL}$ ; $V_{CC} = 4.5 \text{ V}$								
	output voltage	I <sub>O</sub> = -20 μA	4.4	4.5	-	4.4	-	4.4	-	V
		$I_O = -4 \text{ mA}$	3.98	4.32	-	3.84	-	3.7	-	V
$V_{OL}$	LOW-level	$V_I = V_{IH}$ or $V_{IL}$ ; $V_{CC} = 4.5 \text{ V}$								
	output voltage	Ι <sub>Ο</sub> = 20 μΑ		0	0.1	-	0.1		0.1	V
		I <sub>O</sub> = 4.0 mA	-	0.15	0.26	-	0.33	-	0.4	V
l <sub>l</sub>	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 5.5 \text{ V}$	-	-	±0.1		±1.0	-	±1.0	μΑ
I <sub>OZ</sub>	OFF-state output current	$V_I = V_{IH}$ or $V_{IL}$ ; $V_O = V_{CC}$ or GND; $V_{CC} = 5.5 \text{ V}$	-	-	±0.5		±5.0	-	±10	μΑ
I <sub>CC</sub>	supply current	$V_1 = V_{CC}$ or GND; $I_0 = 0$ A; $V_{CC} = 5.5 \text{ V}$	-	-	8.0	-	80	-	160	μΑ
Δl <sub>CC</sub>	additional supply current	$V_1 = V_{CC} - 2.1 \text{ V};$ other inputs at $V_{CC}$ or GND; $V_{CC} = 4.5 \text{ V}$ to 5.5 V; $I_O = 0 \text{ A}$								
		per input pin; 1An inputs	/-	70	252	-	315	-	343	μΑ
		per input pin; 2An inputs	- /	70	252	-	315	-	343	μΑ
		per input pin; nE inputs	-/	135	486	-	607.5	-	661.5	μΑ
C <sub>I</sub>	input capacitance		-	3.5	Ē	CT	RC	N	IC	pF

### 10. Dynamic characteristics

Table 7. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V);  $C_L = 50 \text{ pF}$  unless otherwise specified; for test circuit see Figure 8.

Symbol	Parameter	Conditions	T <sub>an</sub>	<sub>nb</sub> = 25	°C		T <sub>amb</sub> = -40 °C to +85 °C		T <sub>amb</sub> = -40 °C to +125 °C	
			Min	Тур	Max	Min	Max	Min	Max	
74HC139	9									
t <sub>pd</sub>	propagation	nAn to $n\overline{Y}$ n; see Figure 6								
	delay	V <sub>CC</sub> = 2.0 V	-	39	145	-	180	<i>J</i> -	220	ns
		V <sub>CC</sub> = 4.5 V	-	14	29	-	36	-	44	ns
		$V_{CC} = 5.0 \text{ V}; C_L = 15 \text{ pF}$	-	11		-		-	-	ns
		$V_{CC} = 6.0 \text{ V}$	-	11	25	-	31	-	38	ns
		$n\overline{E}$ to $n\overline{Y}n$ ; see Figure 7 1								
		$V_{CC} = 2.0 \text{ V}$	-	33	135	-	170	-	205	ns
		$V_{CC} = 4.5 \text{ V}$	-	12	27	-	34	-	41	ns
		$V_{CC} = 5.0 \text{ V}; C_L = 15 \text{ pF}$		10	-	-	-	-	-	ns
		V <sub>CC</sub> = 6.0 V	-	10	23	-	29		35	ns
t <sub>t</sub>	transition time	n\overline{Y}n; see \overline{Figure 6} and \overline{2} \overline{Figure 7}								
		V <sub>CC</sub> = 2.0 V	-	19	75	-/	95	-	110	ns
		V <sub>CC</sub> = 4.5 V	-	7	15	<i>-</i>	19	-	22	ns
		V <sub>CC</sub> = 6.0 V	-	6	13	-	16	-	19	ns
C <sub>PD</sub>	power dissipation capacitance	$C_L = 50 \text{ pF; } f = 1 \text{ MHz;}$ $V_I = \text{GND to } V_{CC}$	-	42	-	-	-	-	-	pF
74HCT13	39									
t <sub>pd</sub>	propagation	nAn to $\overline{Y}$ n; see Figure 6 [1]								
	delay	V <sub>CC</sub> = 4.5 V		16	34	-	43	-	51	ns
		$V_{CC} = 5.0 \text{ V}; C_L = 15 \text{ pF}$	/-	13		-	-	-	-	ns
		nE to nYn; see Figure 7								
		V <sub>CC</sub> = 4.5 V	-/	16	34	-	43	-	51	ns
		$V_{CC} = 5.0 \text{ V}; C_L = 15 \text{ pF}$	-	13	_					ns
t <sub>t</sub>	transition time	n\overline{Y}n; see Figure 6 and Figure 7			E	GI	RC	N	I C	
		V <sub>CC</sub> = 4.5 V	-	7	15	-	19	-	22	ns

#### Table 7. Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V);  $C_L = 50 \text{ pF}$  unless otherwise specified; for test circuit see Figure 8.

Symbol	Parameter	Conditions		T <sub>amb</sub> = 25 °C		T <sub>amb</sub> = -40 °C to +85 °C		T <sub>amb</sub> = -40 °C to +125 °C		Unit
			Min	Тур	Max	Min	Max	Min	Max	
C <sub>PD</sub>	power dissipation capacitance	$C_L = 50 \text{ pF; } f = 1 \text{ MHz;}$ $V_I = \text{GND to } V_{CC} - 1.5 \text{ V}$	-	44	-	-	-	-	-	pF

- [1]  $t_{pd}$  is the same as  $t_{PLH}$  and  $t_{PHL}$ .
- [2]  $t_t$  is the same as  $t_{THL}$  and  $t_{TLH}$ .
- [3]  $C_{PD}$  is used to determine the dynamic power dissipation ( $P_D$  in  $\mu W$ ).

 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \sum (C_L \times V_{CC}^2 \times f_o)$  where:

f<sub>i</sub> = input frequency in MHz;

f<sub>o</sub> = output frequency in MHz;

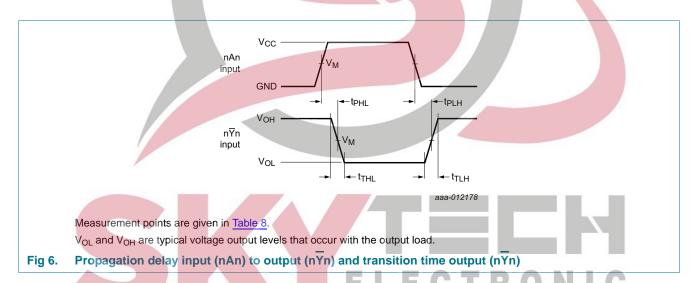
C<sub>L</sub> = output load capacitance in pF;

V<sub>CC</sub> = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_0) = \text{sum of outputs.}$ 

#### 11. Waveforms



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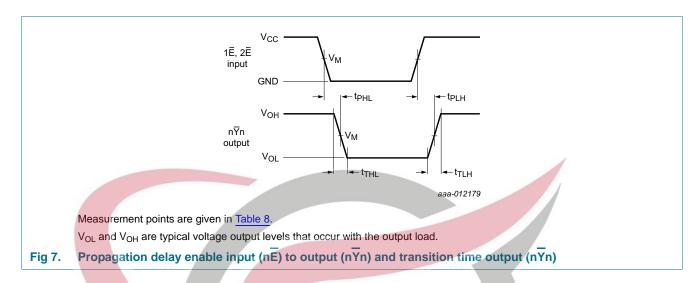


Table 8. Measurement points

Туре		Input	Output		
		V <sub>M</sub>	V <sub>M</sub>		
74HC139		0.5V <sub>CC</sub>	0.5V <sub>CC</sub>		
74HCT139		1.3 V	1.3 V		



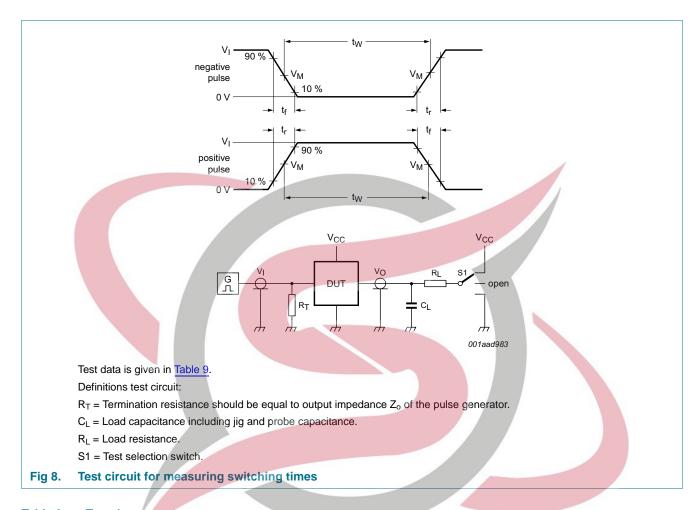


Table 9. Test data

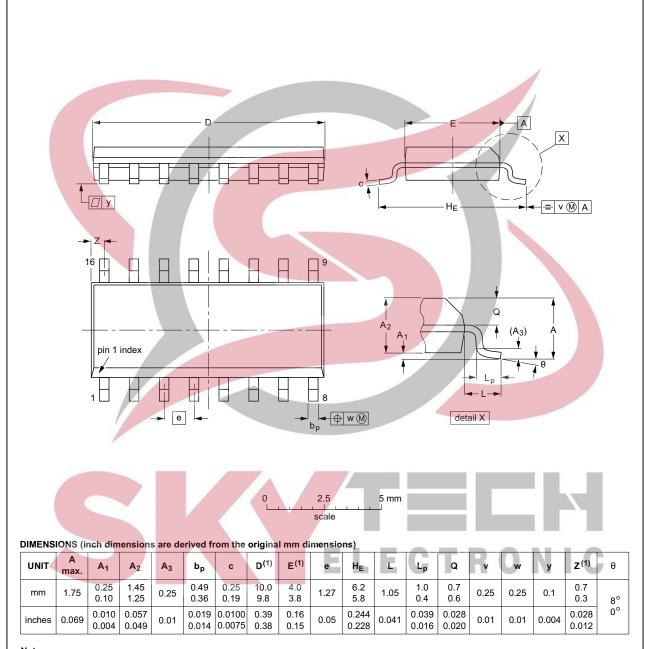
Туре	Input		Load		S1 position		
2000	Vı	t <sub>r</sub> , t <sub>f</sub>	CL	$R_L$	t <sub>PHL</sub> , t <sub>PLH</sub>	t <sub>PZH</sub> , t <sub>PHZ</sub>	t <sub>PZL</sub> , t <sub>PLZ</sub>
74HC139	V <sub>CC</sub>	6 ns	15 pF, 50 pF	1 kΩ	open	GND	V <sub>CC</sub>
74HCT139	3 V	6 ns	15 pF, 50 pF	1 kΩ	open	GND	V <sub>CC</sub>

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### 12. Package outline



SOT109-1



#### Note

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

OUTLINE		REFER	RENCES	EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE	
SOT109-1	076E07	MS-012			<del>99-12-27</del> 03-02-19	

Fig 9. Package outline SOT109-1 (SO16)

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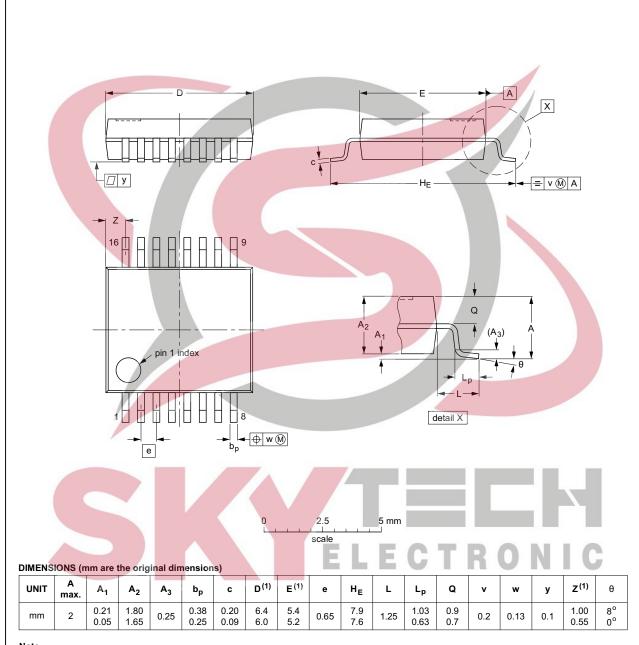
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**Product data sheet** 

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SSOP16: plastic shrink small outline package; 16 leads; body width 5.3 mm

SOT338-1



#### Note

1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

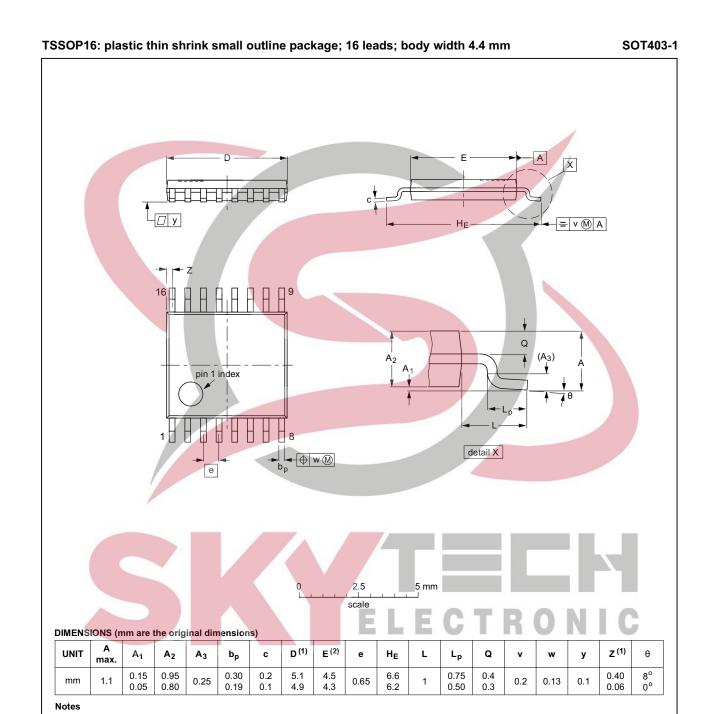
OUTLINE	REFERENCES				EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT338-1		MO-150				<del>99-12-27</del> 03-02-19

Fig 10. Package outline SOT338-1 (SSOP16)

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2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

<sup>1.</sup> Plastic or metal protrusions of 0.15 mm maximum per side are not included.

OUTLINE	REFERENCES				EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT403-1		MO-153				<del>99-12-27</del> 03-02-18

Fig 11. Package outline SOT403-1 (TSSOP16)

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### 13. Abbreviations

#### Table 10. Abbreviations

Acronym	Description
CMOS	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

# 14. Revision history

#### Table 11. Revision history

Document ID	Release date Data shee	t status Change notice	Supersedes
74HC_HCT139 v.4	20151211 Product da	ta sheet -	74HC_HCT139 v.3
Modifications:	Type numbers 74HC139	N and 74HCT139N (SOT38-4) r	emoved.
74HC_HCT139 v.3	20140328 Product da	ta sheet -	74HC_HCT139 v.2
Modifications:	<ul> <li>The format of this data sk guidelines of NXP Semic</li> </ul>	neet has been <mark>redesigned</mark> to cor conductors.	nply with the new identity
	Legal texts have been according to the control of the control	dapted to th <mark>e new comp</mark> any nam	e where appropri <mark>ate.</mark>
74HC_HCT139_CNV v.2	19930927 Product sp	ecification -	-



### 15. Legal information

#### 15.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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